

AXPM450xyz

150/300/500mA, Low VIN, Low VOUT
Ultra-low Dropout NMOS Regulator



Preliminary Datasheet — Feb 2022

Description

AXPM450xyz is a high accuracy, low quiescent current and ultra-low dropout regulator (LDO) that can source 500mA. Its NMOS pass transistor is biased by a dedicated VBIAS pin allowing for ultra-low dropout performance at very low input voltages.

This enables increased efficiency and together with its low quiescent current, AXPM450xyz is ideal for low power battery-operated, power-sensitive applications. Short circuit current foldback and thermal protection are included. It can be stabilized with a small capacitor at the output, saving on space overheads.

An enable logic control function puts AXPM450xyz in shutdown mode, enabling a total current consumption of less than 0.1µA. Device options allows for active pull down at the output for discharge when disable.

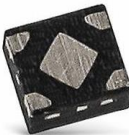
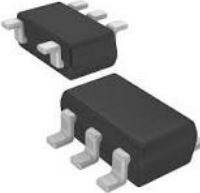
Features

- Input voltage range: 0.8V to 5.5V
- Low quiescent current 25µA (typ) at no load
- Ultra-low dropout 75mV (typ) at 500 mA
- Available in 8 fixed-output voltages: 0.8V, 1.0V, 1.2V, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V
- ±1% VOUT accuracy over Temperature
- High PSRR: 60dB at 1kHz
- Short circuit current limit with foldback
- Thermal shutdown

Applications

- Camera supply
- Mobile phones
- Tablets
- Battery-powered systems

Table 1 Device Summary

Order code			
AXPM450xyz	xx: 08=0.8V, 10=1.0V, 12=1.2V, 15=1.5V, 18=1.8V, 25=2.5V, 28=2.8V, 30=3.0V.		
	y: K=DFN4 epad N=SOT23-5L		
	z: 1=150mA 2=300mA 3=500mA		
		DFN4 epad (1.0 x 1.0 x 0.37)	SOT23-5L (2.9 x 1.6 x 1.1)

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1 Block Diagram and Application Circuit

Figure 1 Block Diagram

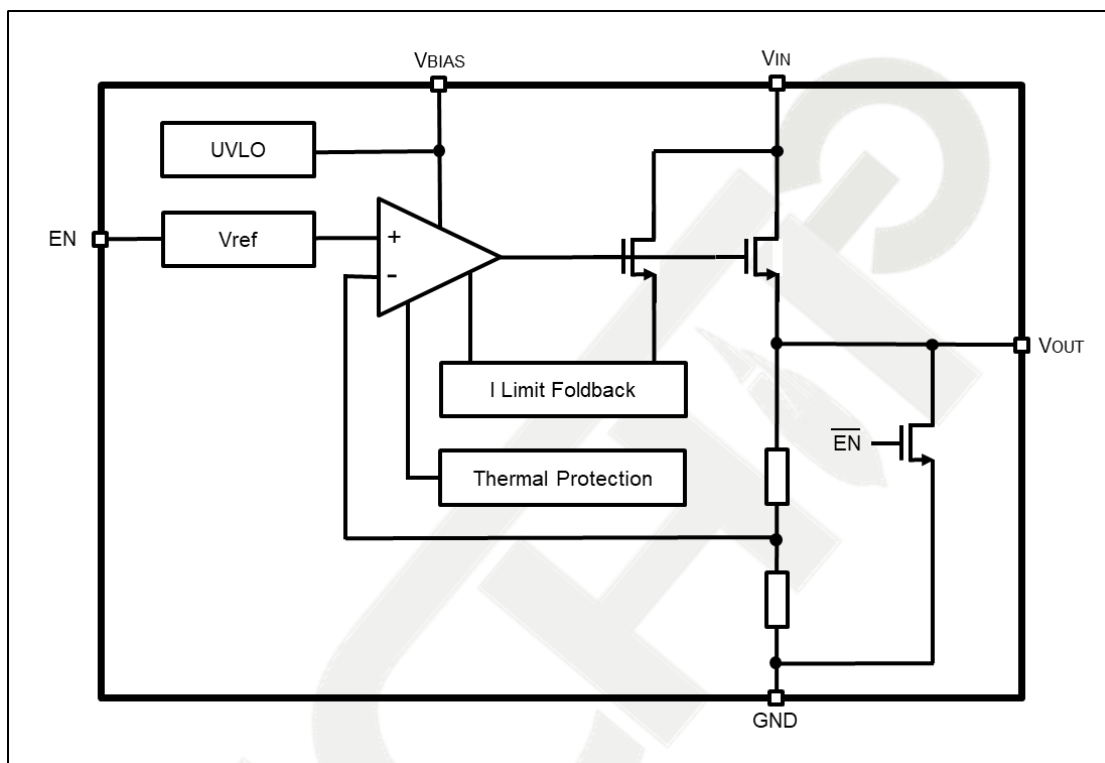
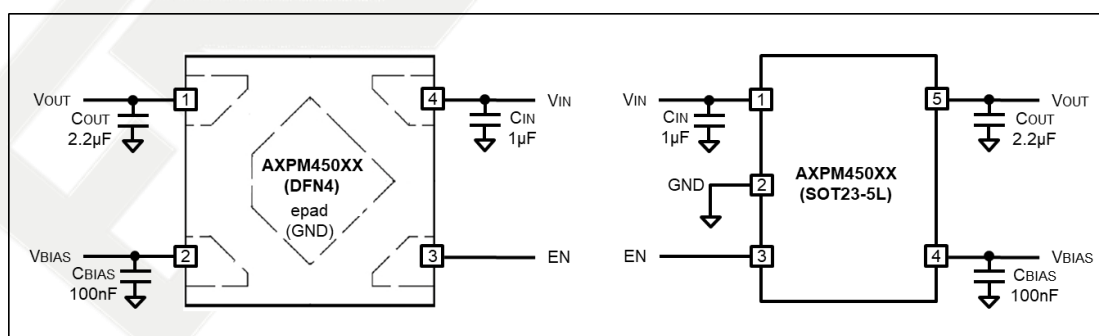


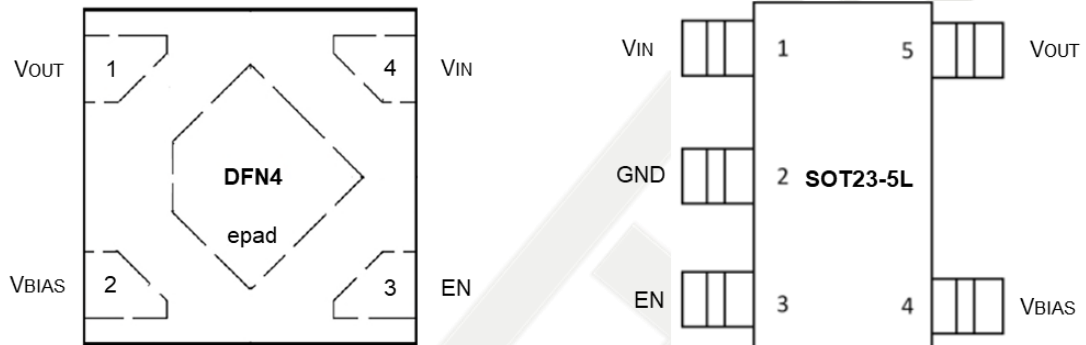
Figure 2 Application Circuit



2 Pin Description

2.1 Pin Names

Figure 3 Pin Connection



2.2 Pin Functions

Table 2 Pin Functions

Pin number (DFN)	Pin number (SOT23-5)	Pin name	Description
1	5	VOUT	Output voltage
2	4	VBIAS	Bias supply input
3	3	EN	Enable pin logic input: low=shutdown, high=active.
4	1	VIN	Input supply voltage
epad	2	GND	Ground

3 Electrical Specifications

3.1 Absolute Maximum Ratings

Table 3 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{IN}	Input voltage	-0.3 to +7	V
V _{BIAS}	Input voltage (for driver)	-0.3 to +7	V
V _{OUT}	Output voltage	-0.3 to V _{IN} +0.3	V
V _{EN}	Enable input voltage	-0.3 to +7	V
I _{OUT}	Output current	Internally limited	mA
PD	Power dissipation	Internally limited	mW
T _j	Junction temperature	+150	°C
T _{stg}	Storage temperature range	-55 to +150	°C

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. The functional operation at or over these absolute maximum ratings is not assured.

3.2 Thermal Data

Table 4 Thermal Data

Symbol	Parameter		Value	Unit
R _{th j-amb}	Thermal resistance junction-to-case	DFN4	60	°C/W
		SOT23-5L	70	°C/W
R _{th j-case}	Thermal resistance junction-to-ambient	DFN4	250	°C/W
		SOT23-5L	260	°C/W

3.3 ESD and Latch Up

Table 5 ESD and Latch Up

Symbol	Parameter		Value	Unit
All pins	Electronics Static Discharge protection voltage	HBM	±2,000	V
		CDM	±500	V
All pins	Latch Up JESD78, Class A		≥ 100	mA

3.4 Electrical Characteristics

$V_{BIAS} = 2.7V$ or $V_{OUT} + 1.6V$ (whichever is greater); $V_{IN} = V_{OUT} + 0.3V$; $I_{OUT} = 1mA$; $C_{IN} = 1\mu F$, $C_{OUT} = 2.2\mu F$; $V_{EN} = 1V$; typical values are at $T_{amb} = 25^{\circ}C$; min/max values are at $-40^{\circ}C \leq T_{amb} \leq 85^{\circ}C$, unless otherwise specified.

Table 6 Electrical Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{IN}	Operating input voltage		$V_{OUT} + V_{DROP}$		5.5	V
V_{BIAS}	Operating bias voltage	$V_{OUT} \leq 1V$	2.4		5.5	V
		$V_{OUT} > 1V$	$V_{OUT} + 1.4$		5.5	V
T_{OP}	Operating temperature		-40		+85	$^{\circ}C$
V_{UVLO}	BIAS under-voltage lockout	V_{BIAS} rising		1.6		V
		Hysteresis		0.2		
V_{OUT}	Output voltage accuracy		-0.5		+0.5	%
		$V_{OUT} (nom) + 0.3V \leq V_{IN} \leq V_{OUT} (nom) + 1V$; $2.7V$ or $V_{OUT} (nom) + 1.6V$ (whichever is greater) $\leq V_{BIAS} \leq 5.5V$; $I_{OUT} = 1mA$ to $500mA$; $-40^{\circ}C \leq T_{amb} \leq 85^{\circ}C$	-1.5		+1.5	%
ΔV_{OUT-IN}	V_{IN} line regulation ⁽¹⁾	$V_{OUT} (nom) + 0.3V \leq V_{IN} \leq 5V$; $I_{OUT} = 1mA$		0.02	0.1	%/V
$\Delta V_{OUT-BIAS}$	V_{BIAS} line regulation ⁽¹⁾	$2.7V$ or $V_{OUT} (nom) + 1.6V$ (whichever is greater) $\leq V_{BIAS} \leq 5.5V$; $I_{OUT} = 1mA$		0.01	0.1	%/V
ΔV_{OUT}	Static load regulation	$I_{OUT} = 1mA$ to $500mA$		1.5		mV
V_{DROP}	Dropout voltage	$I_{OUT} = 150mA$; $V_{OUT} = 97\%$ of $V_{OUT} (nom)$		25	75	mV
		$I_{OUT} = 500mA$; $V_{OUT} = 97\%$ of $V_{OUT} (nom)$		80	250	
$V_{DROP-BIAS}$	Dropout voltage	$V_{BIAS} = V_{IN}$; $I_{OUT} = 500mA$		0.9	1.5	V
V_n	Output noise voltage	$V_{OUT} (nom) = 1.05V$; $V_{IN} = 1.5V$ 10Hz to 100kHz; $I_{OUT} = 1mA$		38		μV_{rms}
SVR_{IN}	V_{IN} supply voltage rejection	$V_{IN} = V_{OUT} (nom) + 0.5V \pm V_{RIPPLE}$; $V_{RIPPLE} = 0.2V$, 1kHz; $I_{OUT} = 150mA$;		75		dB

		VBIAS = 2.7V or VOUT + 1.6V (whichever is greater)				
SVR _{BIAS}	VBIAS supply voltage rejection	VBIAS = 2.9V or VOUT + 1.8V (whichever is greater) ± V _{RIIPPLE} ; V _{RIIPPLE} = 0.2V, 1kHz; I _{OUT} = 150mA; V _{IN} = V _{OUT} (nom) + 0.5V		76		dB
I _{BIAS}	VBIAS operating current	I _{OUT} = 0; VBIAS = 2.7V		27	40	μA
I _{Stby-BIAS}	VBIAS standby current	VBIAS input current in OFF MODE: V _{EN} = GND		0.03	1	μA
I _{Stby-IN}	V _{IN} standby current	V _{IN} input current in OFF MODE: V _{EN} = GND		0.03	1	μA
I _{LIM}	Output current limit	V _{OUT} = 0.9 × V _{OUT} (nom)	550	700	1,000	mA
I _{SC}	Short circuit current	V _{OUT} = 0 (foldback protection)		365	500	mA
R _{ON}	Output discharge mosfet			110		Ω
V _{EN}	Enable logic low				0.4	V
	Enable logic high		0.9			
I _{EN}	Enable input current	V _{EN} = 5.5V			400	nA
T _{ON} ⁽²⁾	Turn on time	V _{OUT} (nom) = 1V		110		μs
T _{SD}	Thermal shutdown			160		°C
	Hysteresis			20		°C
C _{OUT}	Output capacitor		1	2.2	22	μF

(1) Not applicable for V_{OUT} (nom) ≥ 5V.

(2) Turn-on time is time measured between the enable input just exceeding V_{EN} high value and the output voltage just reaching 98% of its nominal value.

4 Functional Description

4.1 VBIAS Voltage Requirement

VBIAS is used for the driving of the NMOS pass channel. The pin must have a minimum voltage of 2.4V and 1.6V (typically) higher than the output for proper operation. In the event VIN supply is meeting the bias requirement, VBIAS can be connected directly to VIN.

4.2 Output Discharge Function

A discharge mosfet is available at VOUT for quick discharge of the output capacitor when device is disabled (EN = low). Optional devices are also available without this discharge mosfet function.

4.3 Short Circuit and Current Limitation

Short circuit current limit foldback protection is integrated. The load current is limited to ILIM when VOUT is equal to 90% of its nominal value. On further decreasing VOUT due to low impedance short circuit, foldback circuit starts operating, limiting the current to ISC when VOUT = 0.

4.4 Thermal Protection

AXPM450xyz is protected with thermal shutdown when the junction temperature reaches 160°C typical. It recovers upon cooling and reaching thermal hysteresis value.

4.5 Input and Output Capacitors

External capacitors are required to ensure the regulator control loop stability. For the input and outputs capacitors, a minimum of 1μF for CIN, a minimum of 100nF for CBIAS and a minimum of 1μF (with ESR 3 to 300mΩ) for COUT are required.

Good quality ceramic capacitors such as the X5R and the X7R are suggested. Further care in placing capacitors close to the pins with low impedance routing and with good return Analog ground minimization of noise pickup. Along with good capacitors having low variations across operation conditions, excellent performance can be achieved with AXPM450xyz.

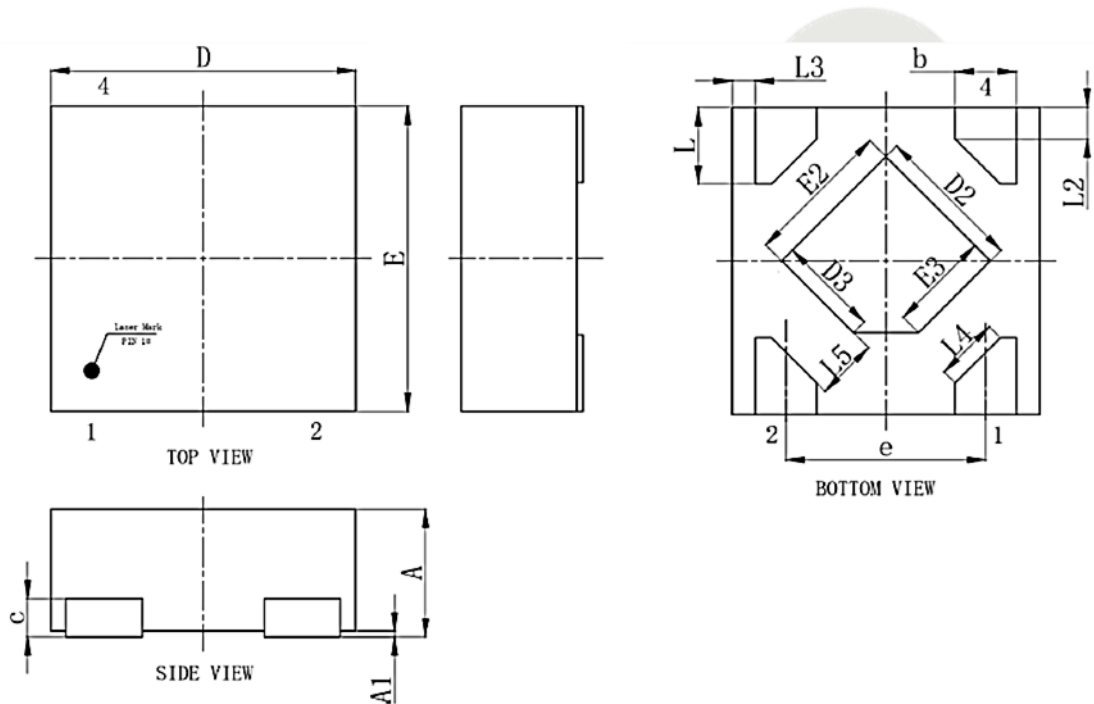
4.6 Under-voltage Lockout (UVLO)

An under-voltage lockout function for VBIAS is included. On powering up, lockout is maintained till VBIAS reaches 1.6V. A hysteresis of 0.2V is designed in to ensure clean entry and exit from the lockout.

5 Package Information

5.1 DFN4

Figure 4 DFN4 EPAD 1.0 x 1.0 x 0.37 Mechanical Data and Package Dimensions



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.35	-	0.40
A1	0.00	0.02	0.05
b	0.15	0.20	0.25
c	0.127REF		
D	0.95	1.00	1.05
D2	0.38	0.48	0.58
D3	0.23	0.33	0.43
e	0.65BSC		

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
E	0.95	1.00	1.05
E2	0.38	0.48	0.58
E3	0.23	0.33	0.43
L	0.20	0.25	0.30
L2	0.103REF		
L3	0.075REF		
L4	0.208REF		
L5	0.200REF		

Feb 2022

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6 Revision History

Table 7 Document Revision History

Date	Version	Description
Jun 2020	Draft	Preliminary Version